Silicon NPN Power Transistors 2SC1004

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For use in horizontal deflection output stages for color TV receives.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



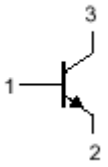


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1100	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.5	A
P_T	Total power dissipation	T_C=25℃	50	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.1A; I_B=0	700			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	I_E=1mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=150m A;I_B=30mA			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=150m A;I_B=30mA			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=800V;I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=4V;I_C=0			10	μA
h_{FE}	DC current gain	I_C=150m A ; V_{CE}=15V	30		160	
f_T	Transition frequency	I_C=150m A ; V_{CE}=15V	2.0			MHz

PACKAGE OUTLINE

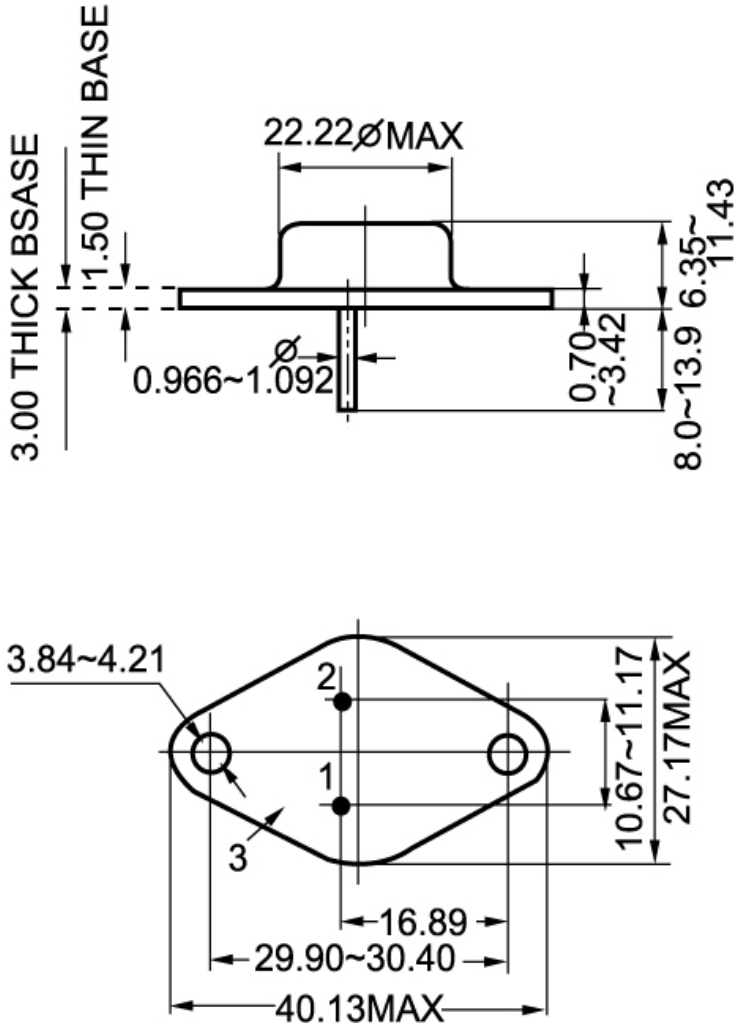


Fig.2 Outline dimensions